

Listing of the Claims

1. (Original) A pre-clean chamber for pre-cleaning a surface prior to metallization of the surface, comprising:

a chamber having a chamber interior;

a wafer heating apparatus provided in said chamber interior for supporting a wafer; and

a source RF power supply operably engaging said chamber for applying source RF energy to said chamber.

2. (Original) The pre-clean chamber of claim 1 further comprising a controller operably engaging said wafer heating apparatus for controlling a temperature of said wafer heating apparatus.

3. (Original) The pre-clean chamber of claim 1 further comprising a bias RF power supply operably connected to said wafer heating apparatus for applying bias RF power to said wafer heating apparatus.

4. (Original) The pre-clean chamber of claim 3 further comprising a controller operably engaging said wafer heating apparatus for controlling a temperature of said wafer heating apparatus.

5. (Original) A pre-clean chamber for pre-cleaning a surface prior to metallization of the surface, comprising:

a chamber having a chamber interior;

a high-temperature electrostatic chuck provided in said chamber interior for supporting a wafer; and

a source RF power supply operably engaging said chamber for applying source RF energy to said chamber.

6. (Original) The pre-clean chamber of claim 5 further comprising a controller operably engaging said chuck for controlling a temperature of said chuck.

7. (Original) The pre-clean chamber of claim 5 further comprising a bias RF power supply operably connected to said chuck for applying bias RF power to said chuck.

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8. (Original) The pre-clean chamber of claim 7 further comprising a controller operably engaging said chuck for controlling a temperature of said chuck.

9. - 20. (Cancelled)